PART 1 Materials



Energy band formation



a) Insulator

b)Semiconductor

c)Conductor





$$n = \int_{\tilde{E}_c}^{E_{au}} f(E) N(E) dE$$



$$n = \int_{\tilde{E}_{c}}^{B_{max}} f(E) N(E) dE$$

$$n = N_{\rm C} \, \exp\left(\frac{E_{\rm F} - E_{\rm C}}{kT}\right)$$



$$np = N_{\rm C}N_{\rm V} \exp\left(\frac{E_{\rm V} - E_{\rm C}}{kT}\right) = N_{\rm C}N_{\rm V} \exp\left(-\frac{E_{\rm s}}{kT}\right)$$

$$np = n_i^2$$

$$N_{\rm C} = 2.86 \times 10^{19} \,{\rm cm}^{-3}$$
 $N_{\rm V} = 3.10 \times 10^{19} \,{\rm cm}^{-3}$ $E_{\rm g} = 1.124 \,{\rm eV}$
 $n_{\rm i} = 1.08 \times 10^{10} \,{\rm cm}^{-3}$

Para silício a 300K



 $E_n = -13.6/n^2$



If we add impurity atoms ND= 10^{16} at/cm³

We will have at room temp $n = 10^{16}$ electrons/cm³

$$p = n_i^2 / N_D^+ = 10^4 \text{ cm}^{-3}$$

In this case n and p are not equal anymore

Since n>>p we call this a n-type semiconductor



$$n = N_{\rm C} \, \exp\left(\frac{E_{\rm F} - E_{\rm C}}{kT}\right)$$

With complete ionization n=N_D

$$N_{\rm D} = N_{\rm C} \exp\left(\frac{E_{\rm F} - E_{\rm C}}{kT}\right)$$



$$E_{\rm F} - E_{\rm C} = kT \ln (N_{\rm D}/N_{\rm C})$$



There are two mechanismos for charge transport

Electric field

Diffusion

$$I = \frac{\Delta Q}{\Delta t}$$

$$I = n \ q \ v_{drift} A$$

 $n A \Delta x$ $\Delta Q = (n A v_d \Delta t) q$

$$j = I_n = n q v_{drift}$$



F= qE F= ma

a= qE/m*

 $V_{drift} = vo + a t_{med}$

Tmed= average time between colisions

$$V_{\rm drift} = -\frac{1}{2} \frac{q}{m_{\rm n}^*} E \overline{t}$$



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Impurity Concentration (cm



$$\frac{\mathrm{d}N}{\mathrm{d}t} = -D_n \frac{\mathrm{d}n(x)}{\mathrm{d}x}$$

 $q \frac{\mathrm{d}n}{\mathrm{d}t} = q D_{\mathrm{n}} \frac{\mathrm{d}n(x)}{\mathrm{d}x}$ I_n

$$I_{\rm n} = q \left(n \,\mu_{\rm n} E + D_{\rm n} \frac{{\rm d}n}{{\rm d}x} \right)$$

 $\frac{kT}{\mu}$ q

GENERATION OF CHARGE



GENERATION OF CHARGE



Depth into cell

CHARGE RECOMBINATION

Radiative

Shockley-Read-Hall

Auger



CHARGE RECOMBINATION





CHARGE RECOMBINATION





